



#### 30V P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	<b>I</b> <sub>D</sub> Τ <sub>A</sub> = +25°C
-30V	$1.5 \Omega @ V_{GS} = -4.5V$	-0.3 A
	2.5 Ω @ V <sub>GS</sub> = -2.5V	-0.2 A

## **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Load Switch
- Portable Applications
- Power Management Functions

### **Features**

- 0.4mm Ultra Low Profile Package for Thin Application
- 0.48mm<sup>2</sup> Package Footprint, 16 Times Smaller Than SOT23
- Low V<sub>GS(th)</sub>, can be Driven Directly from a Battery
- Low R<sub>DS(ON)</sub>
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

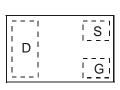
### **Mechanical Data**

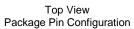
- Case: X2-DFN0806-3
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.00043 grams (Approximate)

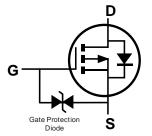












Equivalent Circuit

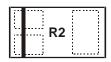
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP32D5LFA-7B	X2-DFN0806-3	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



Top View Bar Denotes Gate and Source Side

R2= Product Type Marking Code



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-0.3 -0.2	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-1.5	А

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

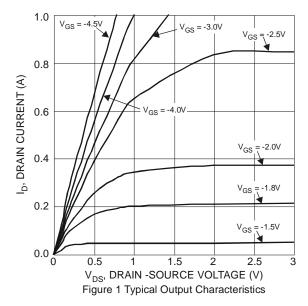
Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	Steady State	P <sub>D</sub>	360	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	353	°C/W
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

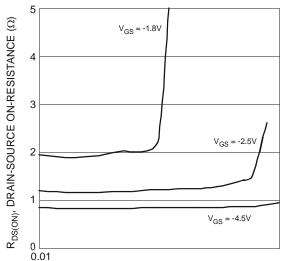
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS	Cymbol		Typ	Max	Oint	rest condition	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-100	nA	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS	·				I.	•	
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.4	_	-1.2	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		_	0.9	1.5	Ω	$V_{GS} = -4.5V, I_D = -200mA$	
Static Drain-Source On-Resistance (Note 7)	R <sub>DS(on)</sub>		1.2	2.5		$V_{GS} = -2.5V, I_D = -100mA$	
			2.5	7.5		$V_{GS} = -1.8V, I_D = -50mA$	
Diode Forward Voltage (Note 8)	$V_{SD}$	_	_	-1.0	V	$V_{GS} = 0V, I_{S} = -10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		40.9	_	pF		
Output Capacitance	Coss		4.7		pF	$V_{DS} = -15V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		3.6	_	pF	1 – 1.000112	
Total Gate Charge	Qg	_	0.7	_	nC	45)/ )/ 45)/	
Gate-Source Charge	Q <sub>gs</sub>	_	0.1	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -15V$ , $I_{D} = -200$ mA	
Gate-Drain Charge	$Q_{gd}$	_	0.2	_	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	_	20	_	ns		
Turn-On Rise Time	t <sub>r</sub>	_	40	_	ns	$V_{DS} = -15V, I_{D} = -200 \text{mA}$	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	144	_	ns	$V_{GS} = -4.5V, R_G = 6\Omega$	
Turn-Off Fall Time	t <sub>f</sub>		58	_	ns	]	

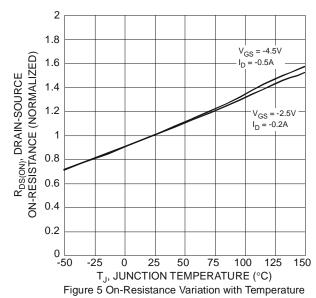
- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to product testing.



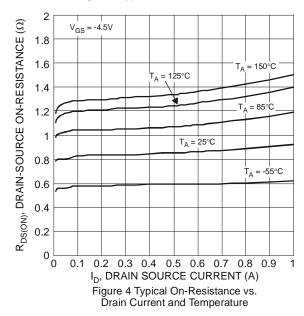


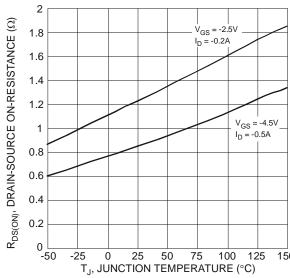


I<sub>D</sub>, DRAIN SOURCE CURRENT (A) Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage



 $V_{DS} = -5.0V$ 0.9 8.0 ID, DRAIN CURRENT (A) 0.7 0.6 0.5 0.4 0.3 0.2 0.1 0 \_ 0.5 1.5 2 2.5 3.5 V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2 Typical Transfer Characteristics







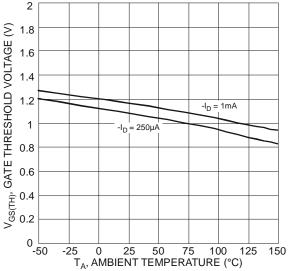
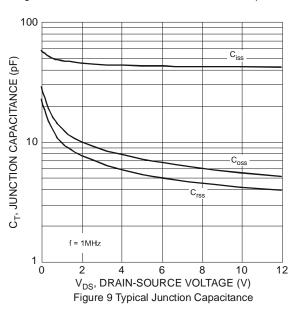
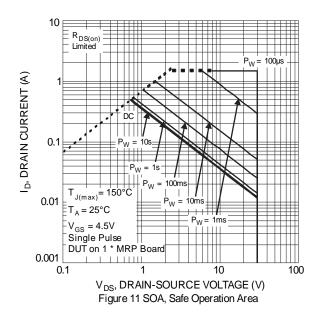
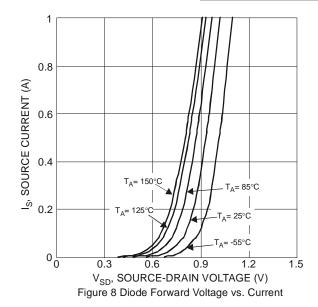
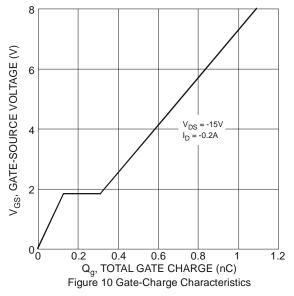


Figure 7 Gate Threshold Variation vs. Ambient Temperature





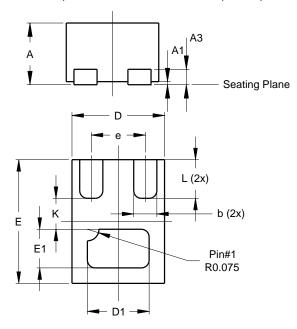






# **Package Outline Dimensions**

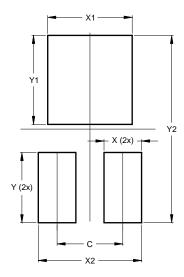
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN0806-3					
Dim	Min	Max	Тур		
Α	0.375	0.40	0.39		
<b>A</b> 1	0	0.05	0.02		
А3	-	ı	0.10		
b	0.10	0.20	0.15		
D	0.55	0.65	0.60		
D1	0.35	0.45	0.40		
Е	0.75	0.85	0.80		
E1	0.20	0.30	0.25		
е	-	-	0.35		
K	-	-	0.20		
L	0.20	0.30	0.25		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value		
Dilliensions	(in mm)		
С	0.350		
Х	0.200		
X1	0.450		
X2	0.550		
Υ	0.375		
Y1	0.475		
Y2	1.000		



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